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SHEET 1 OF 1

INFORMATION DISCLOSURE CITATION PTO-1449		ATTY. DOCKET NO.		SERIAL NO.			
		P102-US		10/627,155			
		APPLICANT Patel, et al					
		FILING DATE 7/24/03		GROUP Not Yet Assigned			
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
	2003/0160540	8/28/03	Miller, et al.				
	6,819,470	11/16/04	Meier, et al.				
	2003/0117688	6/26/03	Meier, et al.				
	2003/0117686	6/26/03	DiCarlo				
	2002/0093721	7/18/02	Kripe				
	6,724,518	4/20/04	Meyer, et al.				
	6,147,790	11/14/00	Meier, et al.				
	6,285,490	9/4/01	Meier, et al.				
	6,523,961	2/25/03	Ilkov, et al.				
	2002/0024641	2/28/02	Ilkov, et al.				
	2004/0004753	1/8/04	Pan				
FOREIGN PATENT DOCUMENTS							
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	WO 2004/001487	12/13/03	PCT			<input type="checkbox"/>	<input type="checkbox"/>
	WO 2004/000720	12/13/03	PCT			<input type="checkbox"/>	<input type="checkbox"/>
	WO 2004/001717	12/13/03	PCT				
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER				DATE CONSIDERED			

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SHEET 1 OF 1

INFORMATION DISCLOSURE CITATION PTO-1449		ATTY. DOCKET NO. P102-US		SERIAL NO. 10/627,155			
		APPLICANT Patel, et al					
		FILING DATE 7/24/03		GROUP Not Yet Assigned			
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
	6,522,454	02/18/03	Meier, et al.				
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INFORMATION DISCLOSURE CITATION PTO-1449 SHEET 1 OF 1		ATTY. DOCKET NO. P102-US		SERIAL NO. 10/627,155			
		APPLICANT Patel, et al					
		FILING DATE 7/24/03		GROUP			
U.S. PATENT DOCUMENTS							
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	5,835,256	11/10/98	Huibers				
	6,046,840	04/04/00	Huibers				
	6,529,310	03/04/03	Huibers, et al.				
	6,396,619	05/28/02	Huibers, et al.				
	6,523,961	02/25/03	Ilkov, et al.				
	2003/0054588	03/20/03	Patel, et al.				
	2004/0125346	07/01/04	Huibers				
	2002/0132389	09/19/02	Patel, et al.				
FOREIGN PATENT DOCUMENTS							
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		APPLICANT Patel, et al.					
		FILING DATE 7/24/03		GROUP Not Yet Assigned			
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
	6,028,690	02/22/00	Carter, et al.				
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PTO/SB/08A (10-01)

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U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

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Substitute for form 1449A/PTO		Completa if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/627,155
		Filing Date	7/24/03
		First Named Inventor	Patel
		Art Unit	Not Yet Assigned
		Examiner Name	Not Yet Assigned
Sheet 1 of 6	Attorney Docket Number	P102-US	

U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No.	Document Number Number - Kind Code ¹ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		US- 3,511,727	05-12-1970	Hays, R.G.	
		US- 4,180,489	02-26-1980	Winters, H.F.	
		US- 4,310,380	12-12-1982	Flamm et al.	
		US- 4,498,953	02-12-1985	Cook et al.	
		US- 6,051,503	04-18-2000	Bhardwai, J.K.	
		US- 6,436,229	08-20-2002	Tai et al.	
		US- 6,182,367	12-19-2000	Tai et al.	
		US- 6,290,864 B1	09-18-2001	Patel et al.	
		US- 6,355,181 B1	03-12-2002	McQuarrie, A.D.	
		US- 2001/0002663 A1	06-07-2001	Tai et al.	
		US- 5,439,553	08-08-1995	Grant et al.	
		US- 2002/0033229 A1	03-21-2002	Leboulz et al.	
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		US- 5,728,480	03-10-1998	Pfister, K.S.	
		US- 2002/0185699	12-12-2002	Rold	
		US- 2002/0121502 A1	09-15-2002	Patel, et al.	
		US- 5,835,258	11-10-1998	Huibers, A.	
		US- 2002/0047172 A1	04-25-2002	Rold	
		US- 2003/0166342 A1	09/04/03	Chinn, et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials ¹	Cite No. ²	Foreign Patent Document Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)	Publication Date ⁶ MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁷
		EP-0704884-A2	04-03-1996	Mehta, J.		
		EP-0822582-A2	02-04-1998	Bhardwal, J.K.		
		EP-0822584-A2	04-04-1998	Bhardwal, J.K.		
		WO-99/49508	09-30-1999	McQuarrie, A.D.		
		EP-0878824-A2	11-18-1998	McQuarrie et al.		
		EP-0878824-A3	01-19-2000	McQuarrie et al.		
		JP-1982/57088679-A	08-18-1982	Tsunetoshi, A.		
		JP-1983/58130529-A	08-04-1983	Yoshihiro et al.		
		JP-1985/60057938-A	04-03-1985	Katsumi et al.		
		WO-98/32183	07-23-1998	Tel et al.		

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Substitute for form 1449A/PTO		Complete if Known:	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary).		Application Number	10/827.155
		Filing Date	7/24/03
		First Named Inventor	Patel
		Art Unit	Not Yet Assigned
		Examiner Name	Not Yet Assigned
Attorney Docket Number	P102-US		
Sheet	2	of	6

U.S. PATENT DOCUMENTS					
Examiner Initials ¹	Cite No. ²	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ³ (if known)			
		US- 6,409,876 B1	06-25-2002	McQuarrie, et al.	
		US- 6,396,619 B1	05-28-2002	Huibers, et al.	
		US- 6,576,489 B2	08/10/03	Leung, et al.	
		US- 6,238,581	05-29-2001	Hawkins, et al.	
		US- 6,116,172	09-05-2000	Jeong	
		US- 6,204,080	03-20-2001	Hwang	
		US- 2003/0071015 A1	04/17/03	Chinn, et al.	
		US- 2002/0184879 A1	11/07/02	Leung, et al.	
		US- 2002/0163051 A1	11/07/02	Gopal, et al.	
		US- 2003/0077878 A1	04/24/03	Kumar, et al.	
		US- 6,197,810 B1	03/06/2001	Toda	
		US- 6,500,356 B2	12/31/02	Goto, et al.	
		US- 2003/0124848 A1	07/03/03	Chinn, et al.	
		US- 2003/0219986 A1	11/27/03	Ratner, et al.	
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FOREIGN PATENT DOCUMENTS						
Examiner Initials ¹	Cite No. ²	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁴
		Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)				
		JP-1997/09251981-A.	09-22-1997	Kazuaki et al.		
		JP-1998/10313128-A	11-24-1998	Hannin et al.		
		JP-1998/10317169-A	12-02-1998	McQuarrie et al.		
		JP-1988/61187238-A	08-20-1988	Nobuo et al.		
		JP-1986/61270830-A	12-01-1986	Toru, T.		
		JP-1987/62071217-A	04-01-1987	Toru et al.		
		JP-1988/63155713-A	06-28-1988	Tadashi, F.		
		JP-1988/61053732-A	03-17-1988	Arata et al.		
		JP-1988/61134019-A	08-21-1988	Shinji et al.		
		JP-1988/61181131-A	08-13-1988	Shinji et al.		

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¹ Applicant's unique citation designation number (optional). ² See Kind Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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Substitute for form 1449B/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/627,155
		Filing Date	7/24/03
		First Named Inventor	Patel
		Group Art Unit	Not Yet Assigned
		Examiner Name	Not Yet Assigned
		Attorney Docket Number	P102-US
Sheet	4	of	6

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		ALIEV et al., "Development of Si(100) Surface Roughness at the Initial Stage of Etching in F2 and XeF2 Gases Ellipsometric Study", Surface Science 442 (1999), pp. 206-214.	
		GLIDEMEISTER, J.M., "Xenon Difluoride Etching System" (Nov. 17, 1997).	
		HABUKA et al., "Dominant Overall Chemical Reaction in a Chlorine Trifluoride-Silicon-Nitrogen System at Atmospheric Pressure", Japan Journal of Applied Physics Vol. 38 (1999), pp. 6468-6469.	
		HECHT et al., "A Novel X-ray Photoelectron Spectroscopy Study of the Al/SiO2 Interface", J. Appl. Phys. Vol. 57 (June 15, 1985), pp. 5258-5261.	
		HOULE, F.A., "Dynamics of SiF4 Desorption During Etching of Silicon by XeF2", IBM Almaden Research Center (April 15, 1987), pp. 1866-1872.	
		FLAMM et al., "XeF2 and F-Atom Reactions with Si: Their Significance for Plasma Etching", Solid State Technol. 26, 117 (1983).	
		IBBOTSON et al., "Plasmaless Dry Etching of Silicon with Fluorine-containing Compounds", J. Appl. Phys. Vol. 56 No. 10 (Nov. 1984), pp. 2939-2942.	
		IBBOTSON et al., "Comparison of XeF2 and F-atom Reactions with Si and SiO2", Applied Physics Letter, Vol. 44, 1129 (1984).	
		STRELLER et al., "Selectivity in Dry Etching of Si (100) and XeF2 and VUV Light", Elsevier Science B.V., Applied Surface Science Vol. 106 (1986), pp. 341-346.	
		VUGTS et al., "Si/XeF2 Etching: Temperature Dependence", J. Vac. Sci. Technol. A 14(5) (Sep/Oct 1996), pp. 2766-2774.	
		WINTERS, H.F., "Etch Products from the Reaction of XeF2 with SiO2, SiO3, Si3N4, SiC, and Si in the Presence of Ion Bombardment", J. Vac. Sci. Technol. B 1(4) (Oct/Dec 1983), pp. 927-931.	

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Substitute for form 1449B/PTO		Complete if Known	
		Application Number	10/827,155
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Filing Date	7/24/03
		First Named Inventor	Patel
		Group Art Unit	Not Yet Assigned
		Examiner Name	Not Yet Assigned
		Attorney Docket Number	P102-US
Sheet	5	of	8

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		Kurt Williams, Etch Rates for Micromachining Processing-Part II, 2003 IEEE, Pgs 761-778, Journal of Microelectromechanical Systems, Vol. 12, No. 6, December 2003.	
		WINTERS et al., "The Etching of Silicon with XeF ₂ Vapor", Appl. Phys. Lett., Vol. 34(1) (January 1, 1979), pp. 70-73.	
		XACTIX, Inc., Marketing Brochure (June 27, 1999).	
		"Xenon Difluoride Isotropic Etch System: Seeing is Believing"; Surface Technology Systems Ltd. brochure, Newport, UK (date unknown).	
		CHU et al., "Controlled Pulse-Etching with Xenon Difluoride", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 1 (June 16 - 19, 1997), pp. 665-668 (abstract only).	
		BASSOM et al., "Modeling and Optimizing XeF ₂ -enhanced FIB Milling of Silicon", 25th International Symposium for Testing and Failure Analysis, Santa Clara, CA (Nov. 14 -18, 1999), pp. 255-261 (abstract only).	
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		CHAN et al., "Gas Phase Pulse Etching of Silicon for MEMS with Xenon Difluoride", Engineering Solutions for the Next Millennium: 1999 IEEE Canadian Conference on Electrical and Computer Engineering, Edmonton, Alberta, Vol. 3 (May 9 - 12, 1999), pp. 1637-1642 (abstract only).	
		CHANG et al., "Gas-Phase Silicon Micromachining with Silicon Difluoride", Proceedings of the SPIE - The International Society for Optical Engineering, Vol. 2641 (1995), pp. 117-128 (abstract only).	

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		Filing Date	7/24/03
		First Named Inventor	Patel
		Group Art Unit	Not Yet Assigned
		Examiner Name	Not Yet Assigned
Sheet	8	of	6
		Attorney Docket Number	P102-US

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cito No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
		SEBEL et al., "Reaction Layer Dynamics in Ion-Assisted Si/XeF ₂ Etching: Temperature Dependence", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 6, (Nov. 2000), pp. 2759-2769 (abstract only).	
		SEBEL et al., "Silicon Etch Rate Enhancement by Traces of Metal", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 17, No. 3, (May/June 1999), pp. 755-762 (abstract only).	
		SUGANO et al., "Study on XeF ₂ Pulse Etching Using Wagon Wheel Pattern", Proceedings of the 1999 International Symposium on Micromechanics and Human Science: Towards the New Century, Nagoya, Japan (Nov. 23 - 26, 1999), pp. 163-167 (abstract only).	
		WANG et al., "Gas-Phase Silicon Etching with Bromine Trifluoride", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 2 (June 16 - 19, 1997), pp. 1505-1508 (abstract only).	
		MUTHUKUMARAN et al., "Gas-Phase Xenon Difluoride Etching of Microsystems Fabricated Through the Mitel 1.5-μm CMOS Process", Can. J. Electr. Comput. Eng. (Canada), Vol. 25, No. 1 (Jan. 2000), pp. 35-41 (abstract only).	
		TOGA et al., "Thin Beam Bulk Micromachining Based on RIE and Xenon Difluoride Silicon Etching", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 1 (June 16 - 19, 1997), pp. 671-674.	
		SEBEL et al., "Etching of Si Through a Thick Condensed XeF ₂ Layer", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 5 (Sept/Oct 2000), pp. 2090-2097 (abstract only).	

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